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FDG311N

N-Channel 2.5V Specified PowerTrench® MOSFET

General Description

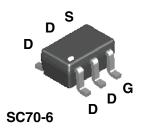
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance. These devices are well suited for portable electronics applications.

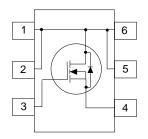
Applications

- Load switch
- Power management
- DC/DC converter

Features

- 1.9 A, 20 V. $R_{DS(ON)}=0.115~\Omega$ @ $V_{GS}=4.5~V$ $R_{DS(ON)}=0.150~\Omega$ @ $V_{GS}=2.5~V$.
- Low gate charge (3nC typical).
- • High performance trench technology for extremely low $R_{\scriptscriptstyle DS/ONI}$.
- Compact industry standard SC70-6 surface mount package.





Absolute Maximum Ratings T_A = 25 C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	1.9	Α
	- Pulsed		6	
P _D	Power Dissipation for Single Operation	(Note 1a)	0.75	W
		(Note 1b)	0.48	
T_J , T_{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

R _e JA	Thermal Resistance, Junction-to-Ambient	(Note 1b)	260	°C/W
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Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity	
.11	FDG311N	7	8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	20			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		14		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 16 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate-Body Leakage Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I _{GSS}	Gate-Body Leakage Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-100	nA
On Chara	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.4	0.9	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_{,J}}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-3		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$\begin{array}{cccccccccccccccccccccccccccccccccccc$		0.082 0.110 0.105	0.115 0.170 0.150	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = 2.5 \text{ V}, I_D = 1.0 \text{ A}$ $V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	4	0.103	0.150	Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 0.5 \text{ A}$		6		S
	Characteristics		ļ	ļ	<u>Į</u>	ļ
C _{iss}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V,	Ì	270		pF
Coss	Output Capacitance	f = 1.0 MHz		55		pF
C _{rss}	Reverse Transfer Capacitance	1		20		pF
Switchin	g Characteristics (Note 2)	-		•		
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$		5	12	ns
t _r	Turn-On Rise Time	$V_{GS} = 5 \text{ V}, R_{GEN} = 6 \Omega$		9	17	ns
t _{d(off)}	Turn-Off Delay Time	†		10	18	ns
t _f	Turn-Off Fall Time	1		2	6	ns
Qg	Total Gate Charge	$V_{DS} = 10 \text{ V}, I_D = 1.9 \text{ A},$		3	4.5	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5 V		0.6		nC
Q _{gd}	Gate-Drain Charge	1		0.9		nC
Drain-So	urce Diode Characteristics	and Maximum Ratings	•	•		•
I _S	Maximum Continuous Drain-Source				0.42	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.42 A (Note 2)		0.7	1.2	V

Notes:

^{1.} $R_{\theta,JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.

a) 170°C/W when mounted on a 1 in²pad of 2oz copper.

b) 260°C/W when mounted on a minimum pad.

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

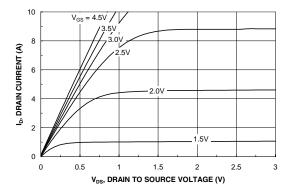


Figure 1. On-Region Characteristics.

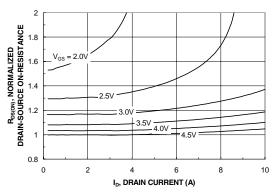


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

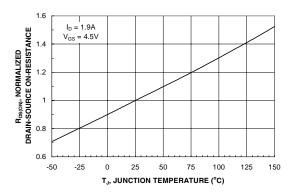


Figure 3. On-Resistance Variation with Temperature.

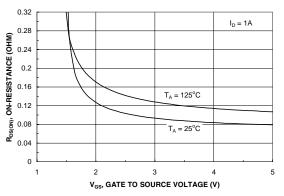


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

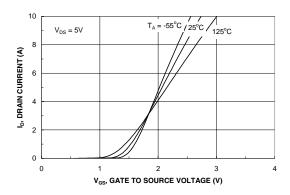


Figure 5. Transfer Characteristics.

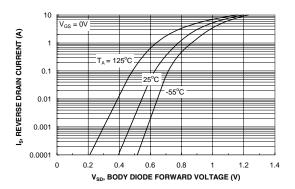


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

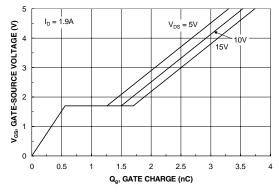


Figure 7. Gate-Charge Characteristics.

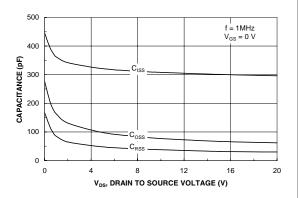


Figure 8. Capacitance Characteristics.

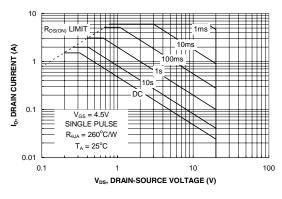


Figure 9. Maximum Safe Operating Area.

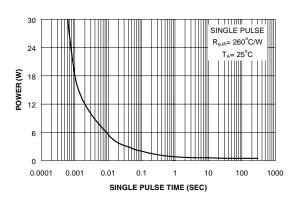


Figure 10. Single Pulse Maximum Power Dissipation.

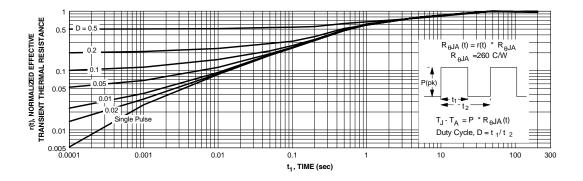


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.



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